

Shinichi Ike

List of Publications by Year in descending order

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papers

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1684188

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#	ARTICLE	IF	CITATIONS
1	Epitaxial GeSn: impact of process conditions on material quality. <i>Semiconductor Science and Technology</i> , 2018, 33, 114010.	2.0	20
2	Characterization of locally strained Ge _{1-x} Sn _x /Ge fine structures by synchrotron X-ray microdiffraction. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	11
3	Epitaxial Ge _{1-x} Sn _x Layers Grown by Metal-Organic Chemical Vapor Deposition Using Tertiary-butyl-germane and Tri-butyl-vinyl-tin. <i>ECS Solid State Letters</i> , 2015, 4, P59-P61.	1.4	10
4	Characterization of crystallinity of Ge _{1-x} Sn _x epitaxial layers grown using metal-organic chemical vapor deposition. <i>Thin Solid Films</i> , 2016, 602, 7-12.	1.8	9
5	Formation and characterization of locally strained Ge _{1-x} Sn _x /Ge microstructures. <i>Thin Solid Films</i> , 2014, 557, 164-168.	1.8	6
6	Analysis of Microscopic Strain and Crystalline Structure in Ge/Ge _{1-x} Sn _x Fine Structures by Using Synchrotron X-ray Microdiffraction. <i>ECS Transactions</i> , 2016, 75, 769-775.	0.5	3
7	Selective epitaxial growth of Ge _{1-x} Sn _x on Si by using metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2017, 468, 614-619.	1.5	3
8	(Invited) Challenges of Energy Band Engineering with New Sn-Related Group IV Semiconductor Materials for Future Integrated Circuits. <i>ECS Transactions</i> , 2015, 69, 89-98.	0.5	2
9	Selective growth of Ge _{1-x} Sn _x epitaxial layer on patterned SiO ₂ /Si substrate by metal-organic chemical vapor deposition. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 01AC05.	1.5	1
10	Epitaxial growth of heavily doped n ⁺ -Ge layers using metal-organic chemical vapor deposition with in situ phosphorus doping. <i>Thin Solid Films</i> , 2018, 645, 57-63.	1.8	1
11	Characterization of Local Strain Structures in Heteroepitaxial Ge _{1-x} Sn _x /Ge Microstructures by Using Microdiffraction Method. <i>ECS Transactions</i> , 2013, 58, 185-192.	0.5	0
12	Influence of precursor gas on SiGe epitaxial material quality in terms of structural and electrical defects. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 04EJ11.	1.5	0
13	In situ phosphorus-doped Ge _{1-x} Sn _x layers grown using low-temperature metal-organic chemical vapor deposition. <i>Semiconductor Science and Technology</i> , 2017, 32, 124001.	2.0	0
14	Evaluation of User Support of a Hemispherical Sub-display with GUI Pointing Functions. <i>Lecture Notes in Computer Science</i> , 2011, , 436-445.	1.3	0